Ordering number:EN3467

N-Channel Silicon MOSFET

2SK1464

Ultrahigh-Speed Switching Applications

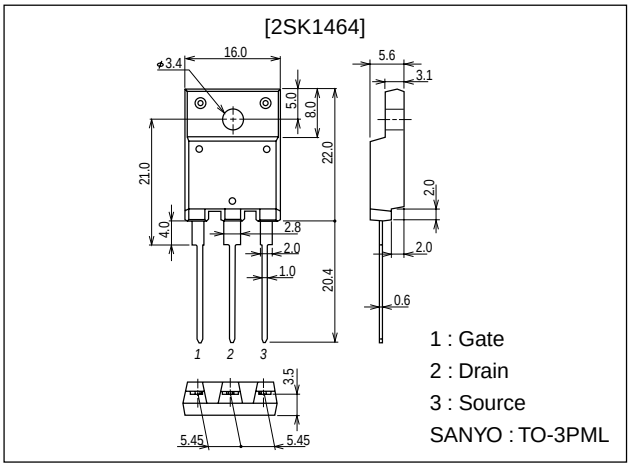
Features

- Low ON-state resistance.
- Ultrahigh-speed switching.
- Converters.

Package Dimensions

unit:mm

2076B



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		900	V
Gate-to-Source Voltage	V_{GSS}		±30	V
Drain Current (DC)	I_D		8	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	16	A
Allowable Power Dissipation	P_D	Tc=25°C	80	W
			3.0	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	900			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=900V, V_{GS}=0			1.0	mA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0			±100	nA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=1mA	2.0		3.0	V
Forward Transfer Admittance	| yfs |	V_{DS}=20V, I_D=4A	2.5	5.0		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	I_D=4A, V_{GS}=10V		1.2	1.6	Ω

(Note) Be careful in handling the 2SK1464 because it has no protection diode between gate and source.

Continued on next page.

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		1600		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		500		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		350		pF
Turn-ON Delay Time	$t_{d(on)}$	I_D=4A, V_{GS}=10V, V_{DD}=200V, R_{GS}=50Ω		20		ns
Rise Time	t_r	I_D=4A, V_{GS}=10V, V_{DD}=200V, R_{GS}=50Ω		80		ns
Turn-OFF Delay Time	$t_{d(off)}$	I_D=4A, V_{GS}=10V, V_{DD}=200V, R_{GS}=50Ω		350		ns
Fall Time	t_f	I_D=4A, V_{GS}=10V, V_{DD}=200V, R_{GS}=50Ω		150		ns
Diode Forward Voltage	V_{SD}	I_S=8A, V_{GS}=0			1.8	V

Switching Time Test Circuit